

SEMICONDUCTOR DEVICE INCLUDING  
MOS FIELD EFFECT TRANSISTOR HAVING  
OFFSET SPACERS OR GATE SIDEWALL FILMS  
ON EITHER SIDE OF GATE ELECTRODE AND  
METHOD OF MANUFACTURING THE SAME

Inventor(s): Hitoshi TSUNO  
DOCKET NO.: 016907-1577

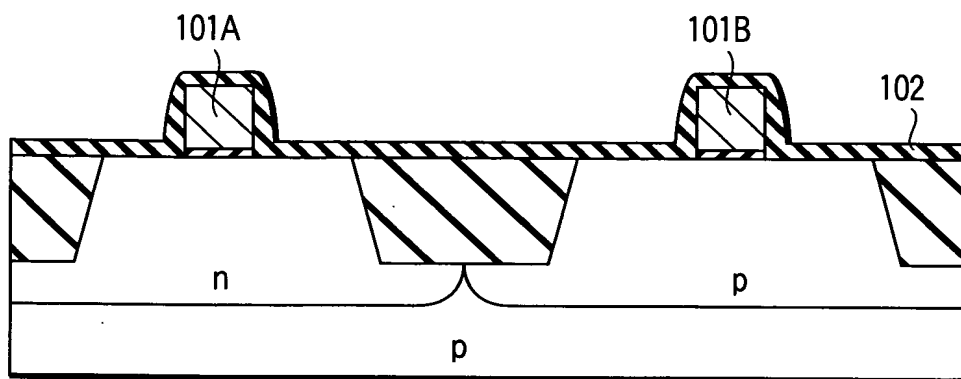


FIG. 1

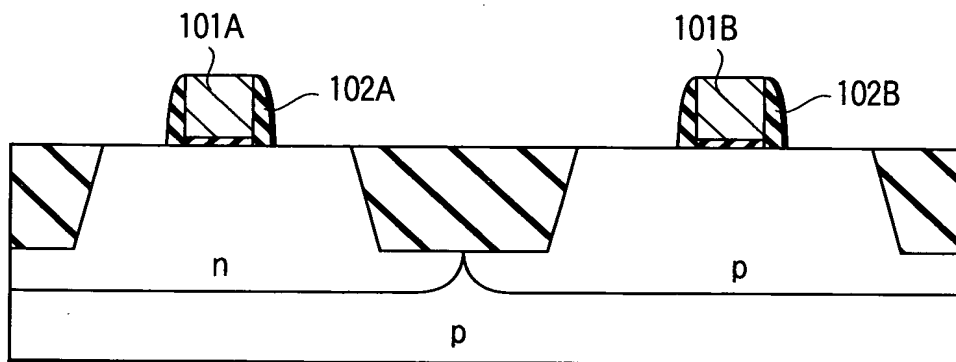


FIG. 2

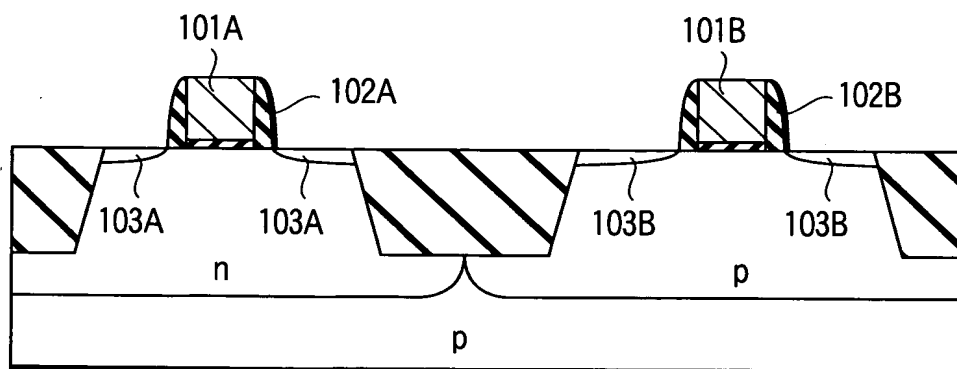


FIG. 3

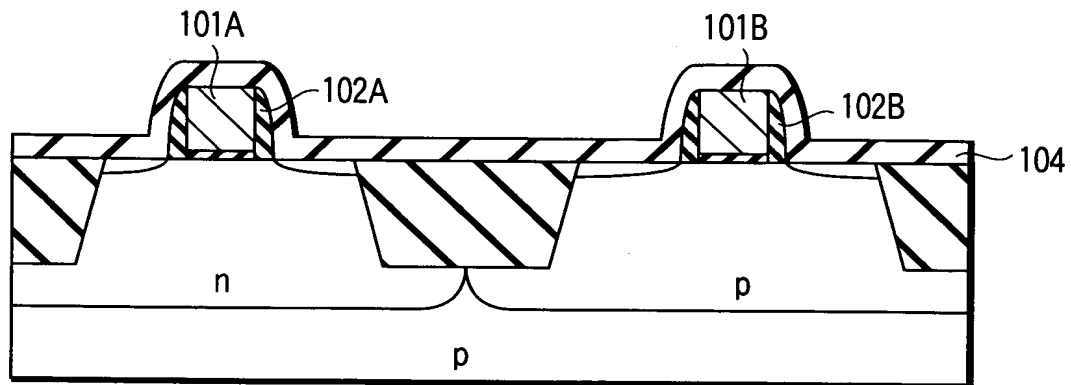


FIG. 4

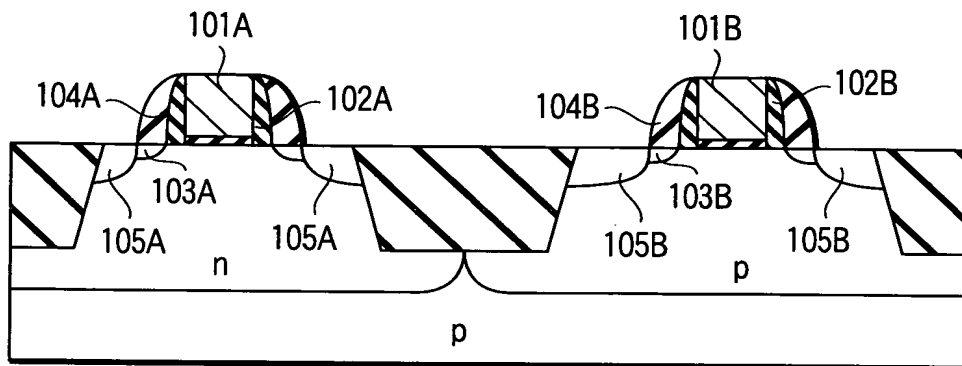


FIG. 5

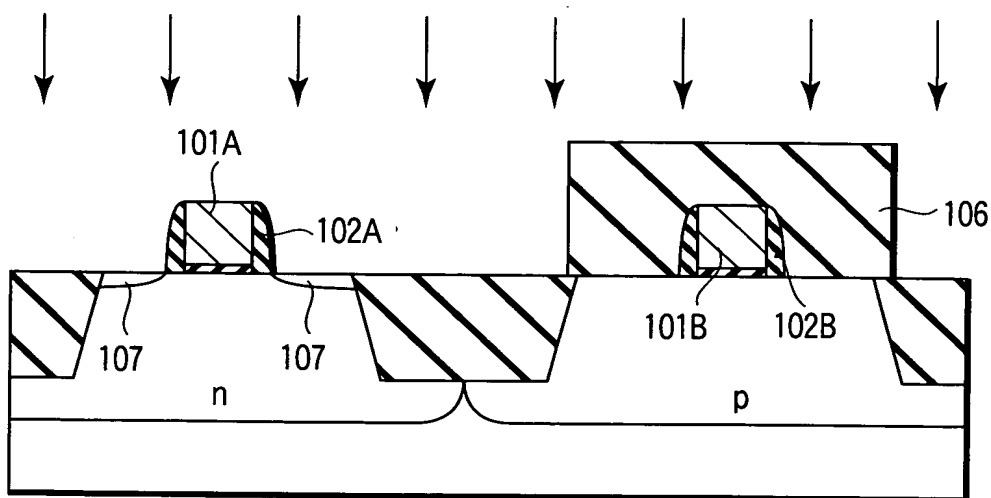


FIG. 6

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THE SEMICONDUCTOR DEVICE INCLUDING

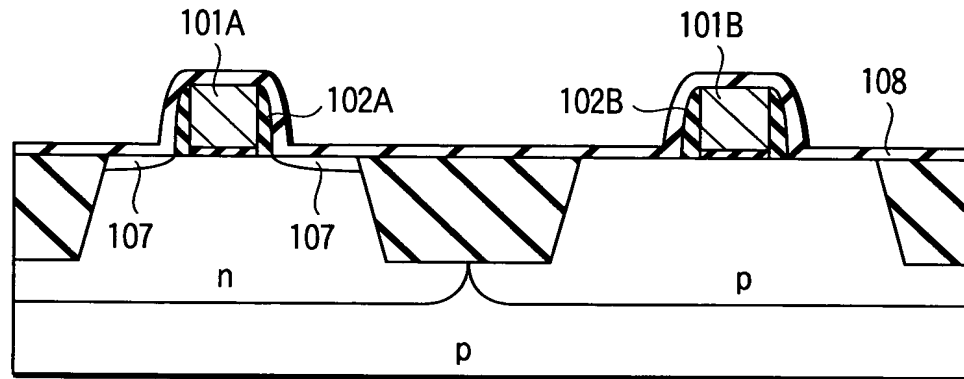


FIG. 7

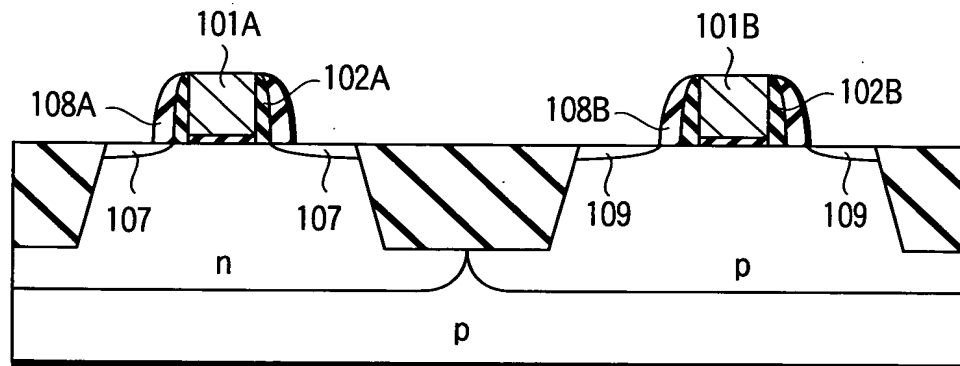


FIG. 8

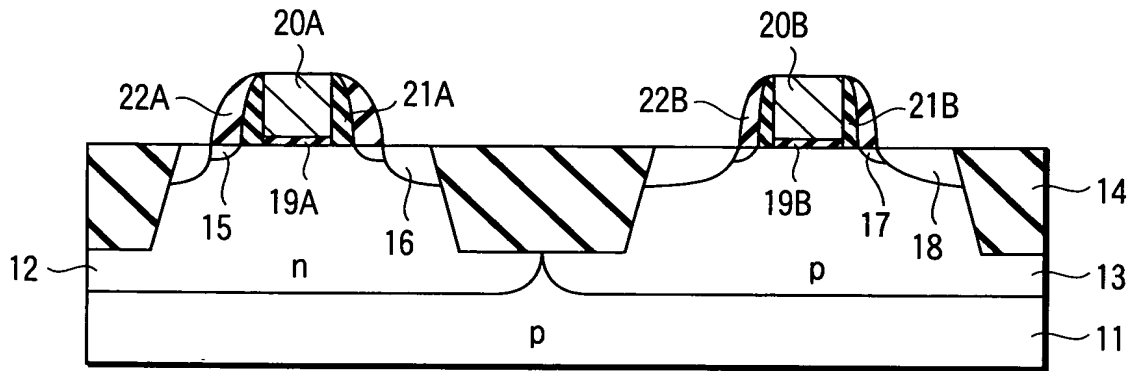


FIG. 9

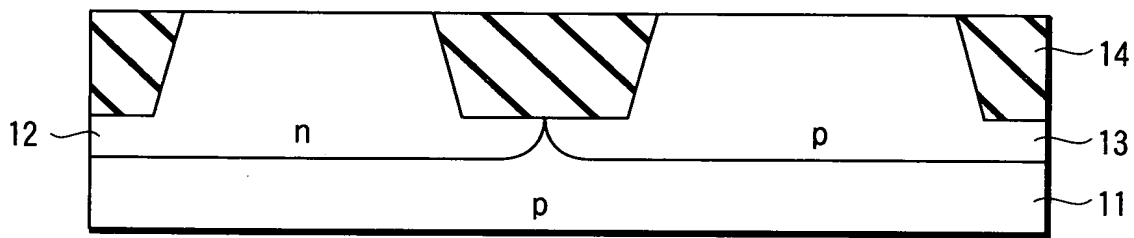


FIG. 10

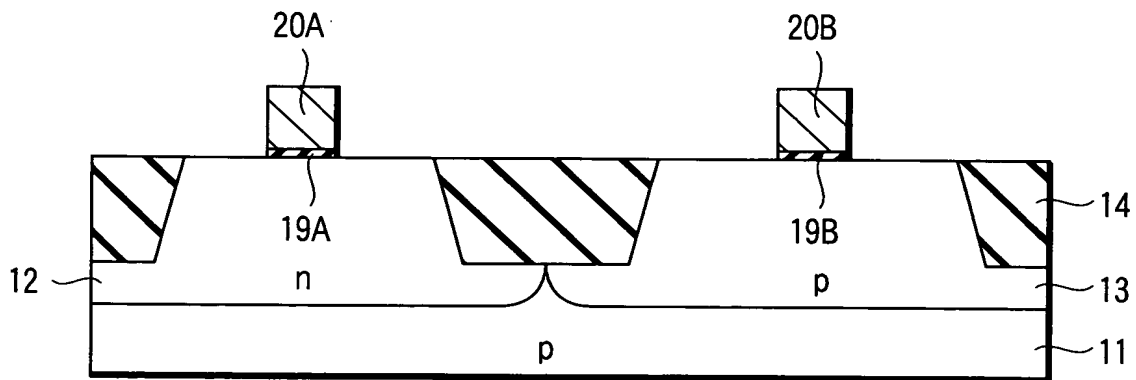


FIG. 11

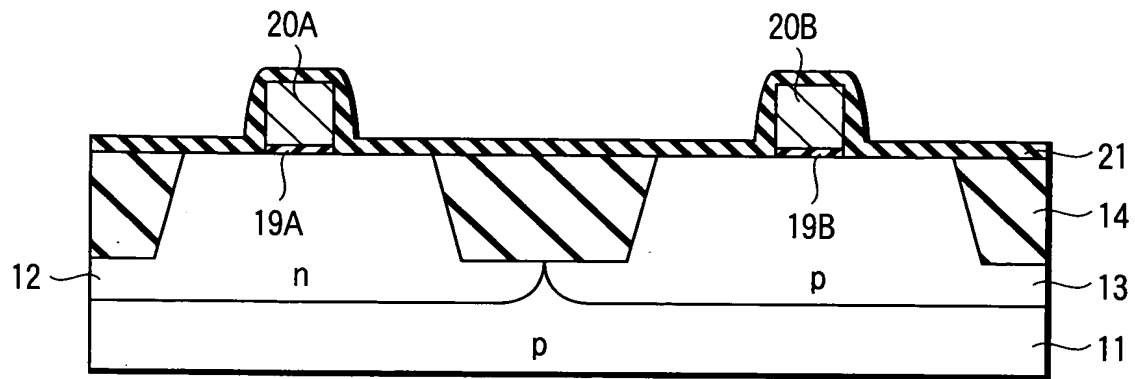


FIG. 12

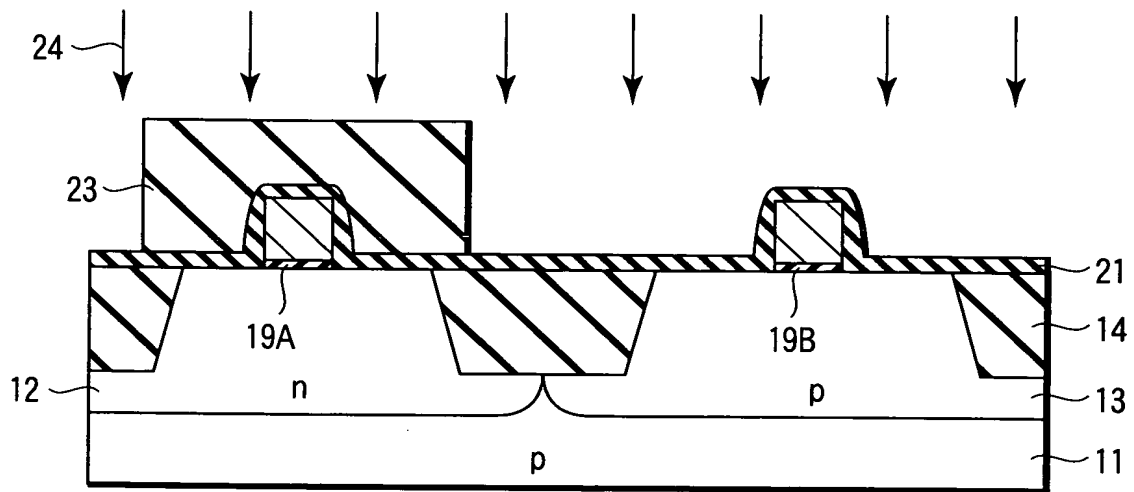


FIG. 13

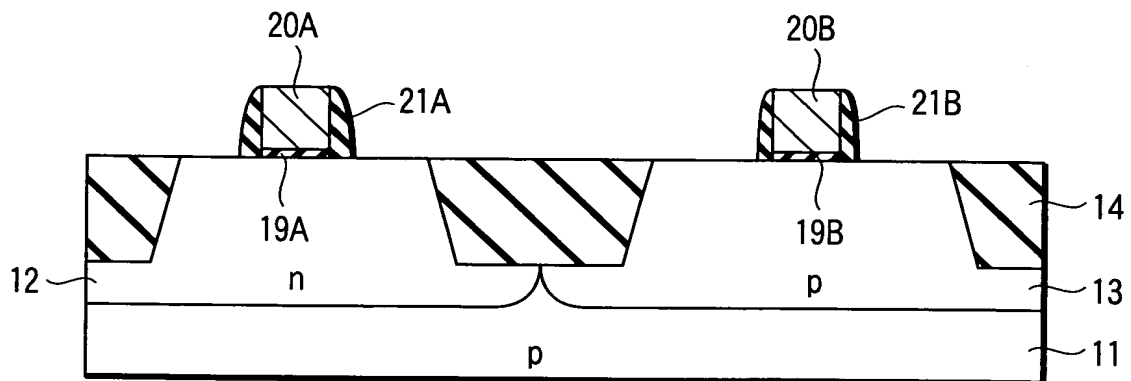


FIG. 14

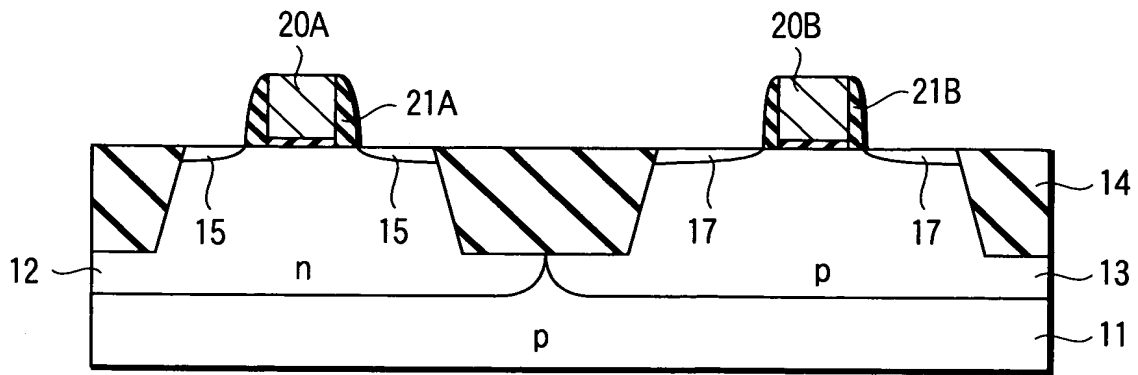


FIG. 15

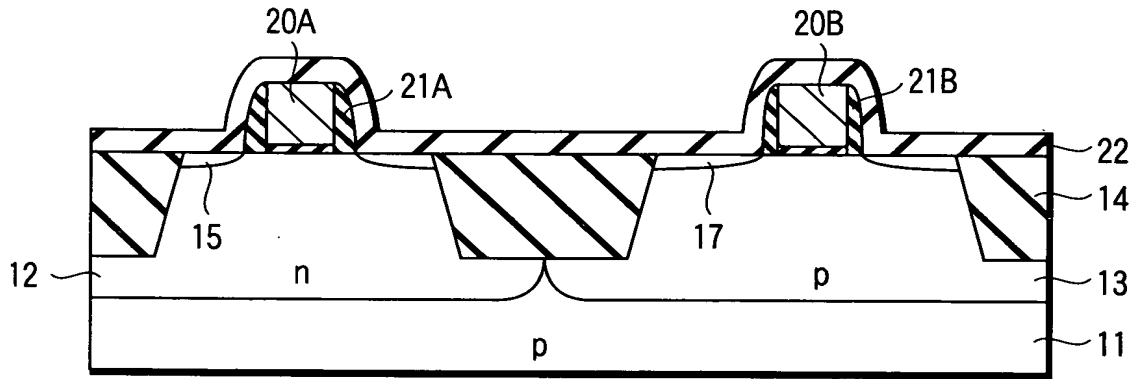


FIG. 16

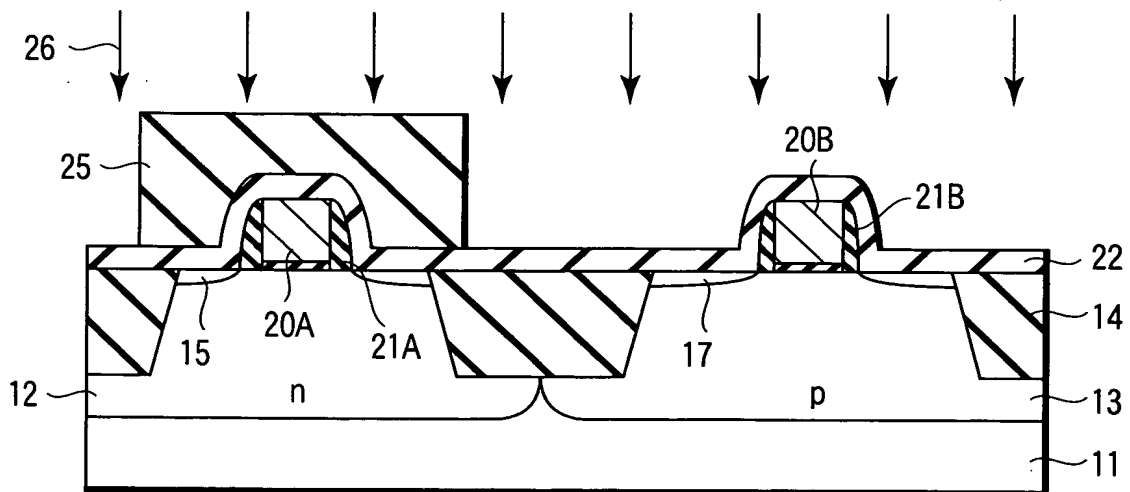


FIG. 17